

IN THE SPECIFICATION:

Please replace paragraphs [0005] and [0006] of the Specifications with the text enclosed in clean form herein below pursuant to 37 C.F.R. §§ 1.121(b)(1)(i) and 1.121(b)(1)(ii). Also attached is a marked-up version of the same paragraphs, as amended herein, pursuant to 37 C.F.R. § 1.121(b)(1)(iii).

[0005] Known overlay targets generally include a pattern formed by one or more etched trenches or pad areas. Illustrated in drawing FIG. 1 is a portion of an intermediate wafer structure 5 including a simple trench-type overlay target 10. The overlay target 10 includes a continuous rectangular trench 11 etched into the semiconductor substrate 14 outside the chip pattern 15. Of course, the overlay target depicted in drawing FIG. 1 is provided for illustrative purposes only. It is understood that overlay targets can be created using a variety of patterns formed from continuous trenches, discontinuous trenches, or pad areas.

B1 [0006] Depicted in drawing FIG. 2 is a cross section taken at line A-A of drawing FIG. 1, illustrating an overlying material layer 16 deposited over the surface 18 of the semiconductor substrate 14 after formation of the trench 11 defining the overlay target. As can be seen in drawing FIG. 2. The overlying material layer 16 tends to conform to the topography created by the trench 11. Such conformation results in the formation of depressions 20 at the upper surface 22 of the overlying material layer 16. Even after a polishing step, portions 24 (shown in drawing FIG. 3) of the depressions 20 may still remain and serve as collection points for process residue 26, such as hemispherical grain ("HSG") Poly. As is shown in drawing FIG. 4, because the residue 26 overlies the trench 11 defining overlay target 10, the residue 26 works to obscure the outlines (depicted by dashed lines 28a and 28b) of the pattern formed by the trench 11, making the outlines 28a and 28b of the overlay target 10 to appear ragged or inconsistent. Though drawing FIG. 2 through drawing FIG. 4 depict features associated with a trench-type overlay target, intermittent collection of obscuring residue is also an issue of pad-type overlay targets and overlay targets including one or more trenches or pads.
